

ABSTRACT OF THE DISCLOSURE

A semiconductor device, namely a lateral MOSFET, facilitates to reduce the on-resistance per unit area. The lateral MOSFET exhibiting a high breakdown voltage includes a semiconductor substrate of a first conductivity type, trenches formed in semiconductor substrate and aligned in the channel in the width direction of the MOSFET, a drain drift region of a second conductivity type surrounding the trenches from the side of the side walls and bottom walls thereof, an insulator in each trench, and a region doped with an impurity of the first conductivity type and extending between the trenches.